Abstracts

One Watt, Very High Efficiency 10 and 18 GHz Pseudomorphic HEMTs Fabricated by Dry First Recess Etching

S. Shanfield, A. Platzker, L. Aucoin, T. Kazior, B.I. Patel, A. Bertrand, W. Hoke and P. Lyman. "One Watt, Very High Efficiency 10 and 18 GHz Pseudomorphic HEMTs Fabricated by Dry First Recess Etching." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 639-641.

We report on record 10 and 18 GHz power performance of double recessed 1.2 mm periphery pseudornorphic HEMTs where the critical first recess was formed with exceptional uniformity using dry etching and an AlGaAs etch stop layer. Simultaneous power, gain, and power-added efficiency, representative of many devices, is summarized below.

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